

ABSTRACT OF THE INVENTION

One embodiment of the invention relates to a polymer memory device and a method of making it. The polymer memory device may include a composite or single layer of a
5 ferroelectric polymer memory that addresses surface engineering needs according to various embodiments. The ferroelectric polymer memory structure may include crystalline ferroelectric polymer layers such as single and co-polymer compositions. The structure may include spin-on and/or Langmuir-Blodgett deposited compositions.

One embodiment of the invention relates to a method making embodiments of the
10 polymer memory device. One embodiment of the invention relates to a memory system that allows the polymer memory device to interface with various existing hosts.

15

BEST AVAILABLE COPY